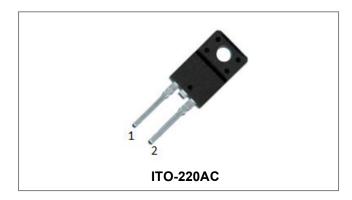






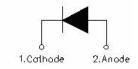
SDURF1060 ULTRAFAST RECTIFIER



Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- · Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- Terminals finish: 100% Pure Tin
- This is a Pb free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	600	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=105°C, rectangular wave form	10	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse,Tc=25°C	100	Α
Power Dissipation	P _D	Tc=25°C	31	W

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	4	°C/W
Approximate Weight	wt	-	1.6	g
Case Style	ITO-220AC			

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Electrical Characteristics:

Characteristics	Symbol	Condition		Max.	Units
Forward Voltage Drop*	V _{F1}	@10A, Pulse, T _J = 25°C	1.66	2.2	V
	V _{F2}	@10A, Pulse, T _J = 125°C	1.58	2.0	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25°C	0.3	10	μA
	I _{R2}	@V _R = rated V _R , T _J = 125°C	150	500	μA
Junction Capacitance(Peg Leg)	Ст	$@V_R = 5V, T_C = 25 ^{\circ}C, f_{SIG} = 1MHz$	50	-	pF
Reverse Recovery Time	t _{rr}	I _F =500mA, I _R =1A,and I _{rm} =250mA	26	32	ns
Reverse Recovery Time	t _{rr}	L = 104 diF/dt = 2004/up	47	70	ns
Reverse Recovery Charge	Qrr	- I _F = 10A, diF/dt = -200A/μs - V _R = 400V, T _J = 25°C	99	-	nC
Reverse Recovery Current	I _{RRM}	VR - 400V, IJ - 25 C	4.2	-	Α
Reverse Recovery Time	t _{rr}	L = 104 diF/dt = 2004/up	68	100	ns
Reverse Recovery Charge	Qrr	- I _F = 10A, diF/dt = -200A/μs - V _R = 400V, T _J = 125°C	185	-	nC
Reverse Recovery Current	I _{RRM}	VR = 400V, 1J = 125 C	5.4	-	Α
Reverse Recovery Time	t _{rr}	- I _F = 1A, di _F /dt = -100A/µs	32	50	ns
Reverse Recovery Charge	Qrr	$V_R = 30V, T_J = 25^{\circ}C$	26	-	nC
Reverse Recovery Current	I _{RRM}	- VR - 30V, TJ - 23 C	1.6	-	Α
Reverse Recovery Time	t _{rr}	L = 10 di /dt = 1000/up	47	-	ns
Reverse Recovery Charge	Qrr	$I_F = 1A$, $di_F/dt = -100A/\mu s$	52	-	nC
Reverse Recovery Current	I _{RRM}	V _R = 30V, T _J = 125°C	2.2	-	Α
Reverse Recovery Time	t _{rr}	1 404 11/11 4004/	51	-	ns
Reverse Recovery Charge	Qrr	l _F = 10A, di _F /dt = -100A/µs - V _R = 30V, T _J = 25°C	64	-	nC
Reverse Recovery Current	I _{RRM}	- VR - 30V, IJ - 23 C	2.5	-	Α
Reverse Recovery Time	t _{rr}	1 - 404 - 4: /-14 - 4004/	70	-	ns
Reverse Recovery Charge	Qrr	l _F = 10A, di _F /dt = -100A/µs - V _R = 30V, T _J = 125°C	123	-	nC
Reverse Recovery Current	I _{RRM}	7 VK - 30V, IJ - 123 C	3.5	-	Α

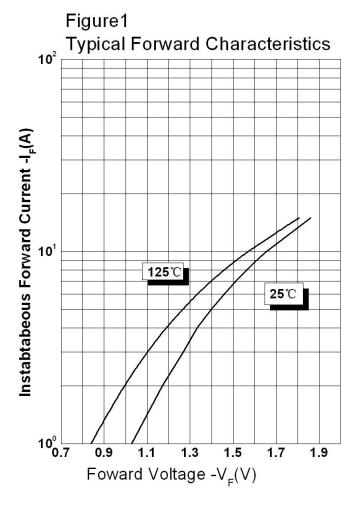
 $^{^{\}star}\,$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%

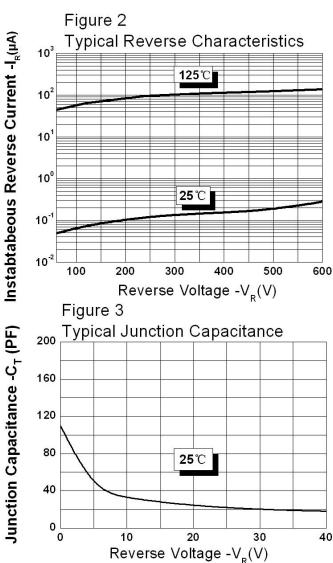






Ratings and Characteristics Curves

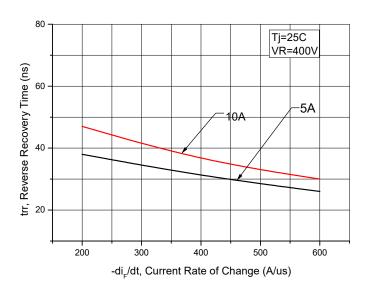












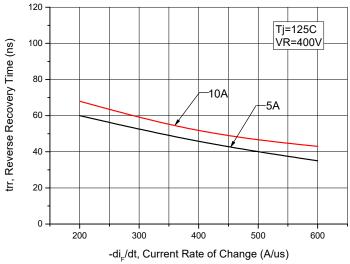


Figure 4. Reverse Recovery Time vs.

Current Rate of Change

Figure 5. Reverse Recovery Time vs.
Current Rate of Change

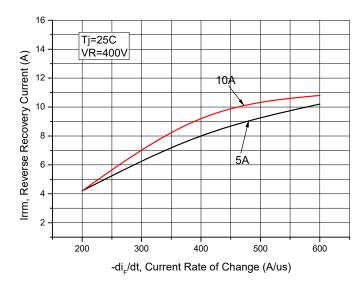


Figure 6. Reverse Recovery Current vs.
Current Rate of Change

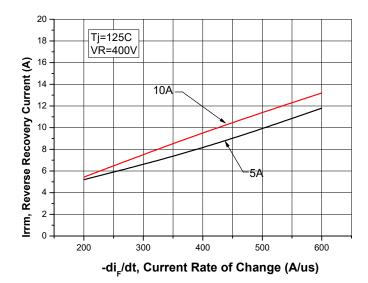


Figure 7. Reverse Recovery Current vs.

Current Rate of Change

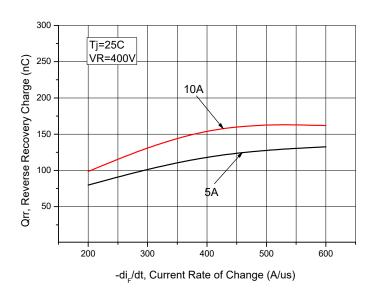
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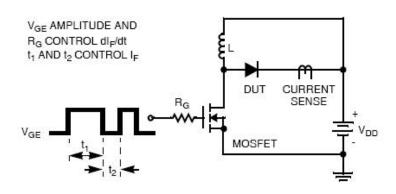




400 Tj=125C VR=400V 350 Qrr, Reverse Recovery Charge (nC) 10A-300 250 200 150 -5A 100 50 0 200 400 500 600 -di_/dt, Current Rate of Change (A/us)

Figure 8. Reverse Recovery Charge vs. Current Rate of Change

Figure 9. Reverse Recovery Charge vs.
Current Rate of Change



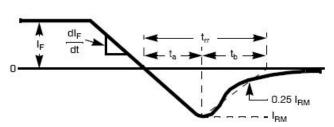


Figure 10. Diode Test Circuit

Figure 11. Diode Reverse Recovery Waveform

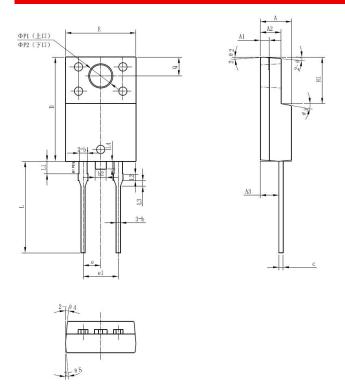
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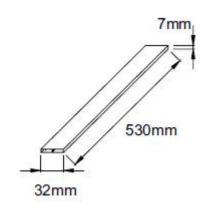


Mechanical Dimensions ITO-220AC

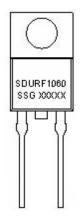


SYMBOL	Millimeters				
STINIBUL	MIN.	TYP.	MAX.		
Α	4.30	4.50	4.70		
A1	1.10	1.30	1.50		
A2	2.80	3.00	3.20		
A3	2.50	2.70	2.90		
b	0.50	0.60	0.75		
b1	1.10	1.20	1.35		
b2	1.50	1.60	1.75		
С	0.55	0.60	0.75		
D	14.80	15.00	15.20		
E	9.96	10.16	10.36		
е	-	2.55	-		
e1	-	5.10	_		
H1	6.50	6.70	6.90		
L	12.70	13.20	13.70		
L1	1.60	1.80	2.00		
L2	0.80	1.00	1.20		
L3	0.60	0.80	1.00		
L4	_	1.10	1.50		
ΦP1 (上口)	3.30	3.50	3.70		
ΦP2 (下口)	2.99	3.19	3.39		
Q	2.50	2.70	2.90		
Θ1		5°			
Θ2		4°			
Θ3		10°			
Θ4		5°			
Θ5		5°			

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

SDUR = Device Type = Package type = Forward Current (10A) = Reverse Voltage (600V) 10 60 SSG = SSG = Year WW

= Week = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping	
SDURF1060	ITO-220AC (Pb-Free)	50 pcs/ tube	

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